**Product data sheet** 

## 1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

### 2. Features and benefits

- Fast switching
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic
- Reduces switching losses in associated MOSFET or IGBT
- · Planar passivated for voltage ruggedness and reliability

## 3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply
- · Motor drive and SMPS freewheeling diode

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	1200	V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5; T <sub>mb</sub> ≤ 98 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	16	A
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 16 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	1.8	2.7	V
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	50	-	ns





# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K — A
2	Α	anode		001aaa020
mb	mb	mounting base; connected to cathode	TO-247 (SOD142)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYR16W-1200	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BYR16W-1200	BYR16W-1200

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

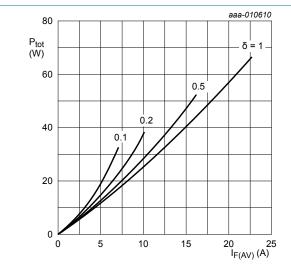
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	1200	V
$V_{RWM}$	crest working reverse voltage		-	1200	V
V <sub>R</sub>	reverse voltage	DC	-	1200	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; $T_{mb} \le$ 98 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	16	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 98 °C$ ; square-wave pulse	-	32	А

BYR16W-1200

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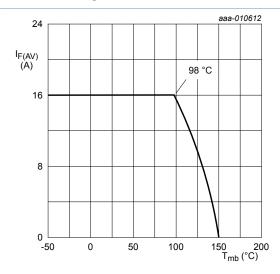
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Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	165	A
T <sub>stg</sub>	storage temperature		-55	150	°C
T <sub>j</sub>	junction temperature		-	150	°C

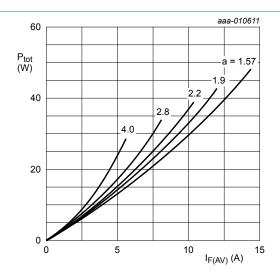


Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} = I_{F(RMS)} \times \sqrt{\pmb{\delta}} \\ V_{\rm O} = 2.210 \text{ V; R}_{\rm S} = 0.032 \text{ }\Omega \end{split}$$

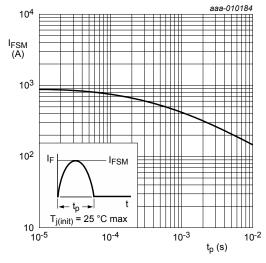


Forward current as a function of mounting base | Fig. 4. temperature; maximum values



Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor = 
$$I_{F(RMS)}/I_{F(AV)}$$
  
 $V_{\odot}$  = 2.210 V;  $R_{S}$  = 0.032  $\Omega$ 



Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	45	-	K/W

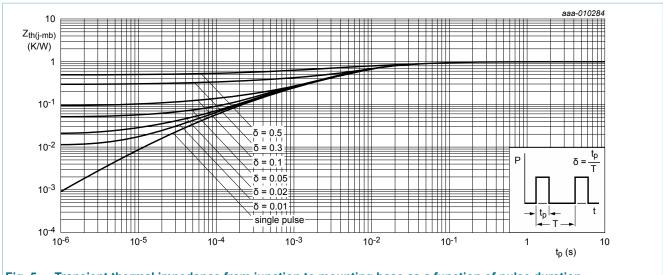


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 16 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.3	3	V
		I <sub>F</sub> = 32 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.8	3.9	V
		I <sub>F</sub> = 16 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	1.8	2.7	V
I <sub>R</sub> rev	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C	-	3	100	μA
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 125 °C	-	0.2	2	mA
Dynamic cl	naracteristics					
Q <sub>r</sub>	recovered charge	$I_F$ = 16 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/ $\mu$ s; $T_j$ = 25 °C; Fig. 7	-	520	-	nC
		$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	1200	-	nC
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 25 \text{ °C}; Fig. 7$	-	605	-	nC	
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	1600	-	nC	
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	40	-	ns	
		$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 \text{ °C}; Fig. 7$	-	90	-	ns	
		$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	150	-	ns	
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	105	-	ns	
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	200	-	ns	
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	-	ns	
RM	peak reverse recovery current	$I_F$ = 16 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/ $\mu$ s; $T_j$ = 25 °C; <u>Fig. 7</u>	-	11.2	-	A	
		$I_F$ = 16 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/ $\mu$ s; $T_j$ = 125 °C; <u>Fig. 7</u>	-	16	-	A	
			$I_F$ = 16 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ $\mu$ s; $T_j$ = 25 °C; $Fig. 7$	-	11.2	-	A
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 125 \text{ °C}; Fig. 7$	-	16.2	-	A	

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### Ultrafast power diode

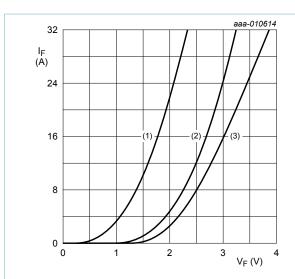


Fig. 6. Forward current as a function of forward voltage

(1)  $T_j = 125$  °C; typical values;

(2)  $T_j = 125$  °C; maximum values;

(3)  $T_j = 25$  °C; maximum values;

 $V_{\rm O} = 2.210 \, \rm V; \, R_{\rm S} = 0.032 \, \Omega$ 

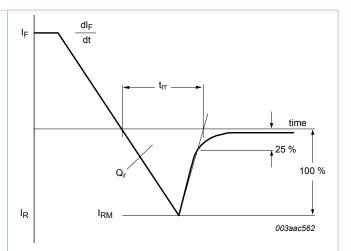
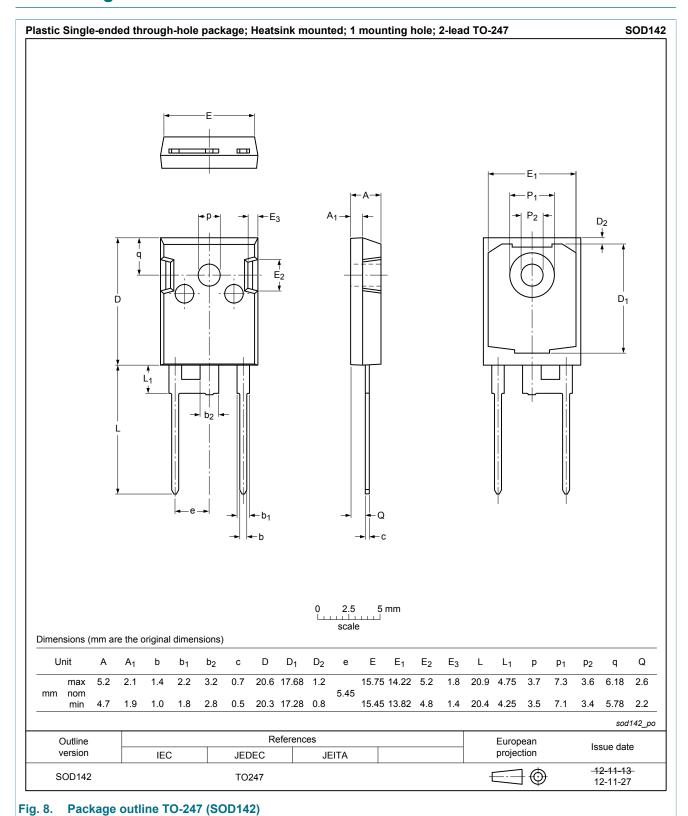


Fig. 7. Reverse recovery definitions; ramp recovery

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## 11. Package outline



## 12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Ultrafast power diode

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